



AVTECH ELECTROSYSTEMS LTD.

NANOSECOND WAVEFORM ELECTRONICS
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□ P.O. BOX 265
OGDENSBURG, NY
U.S.A. 13669-0265

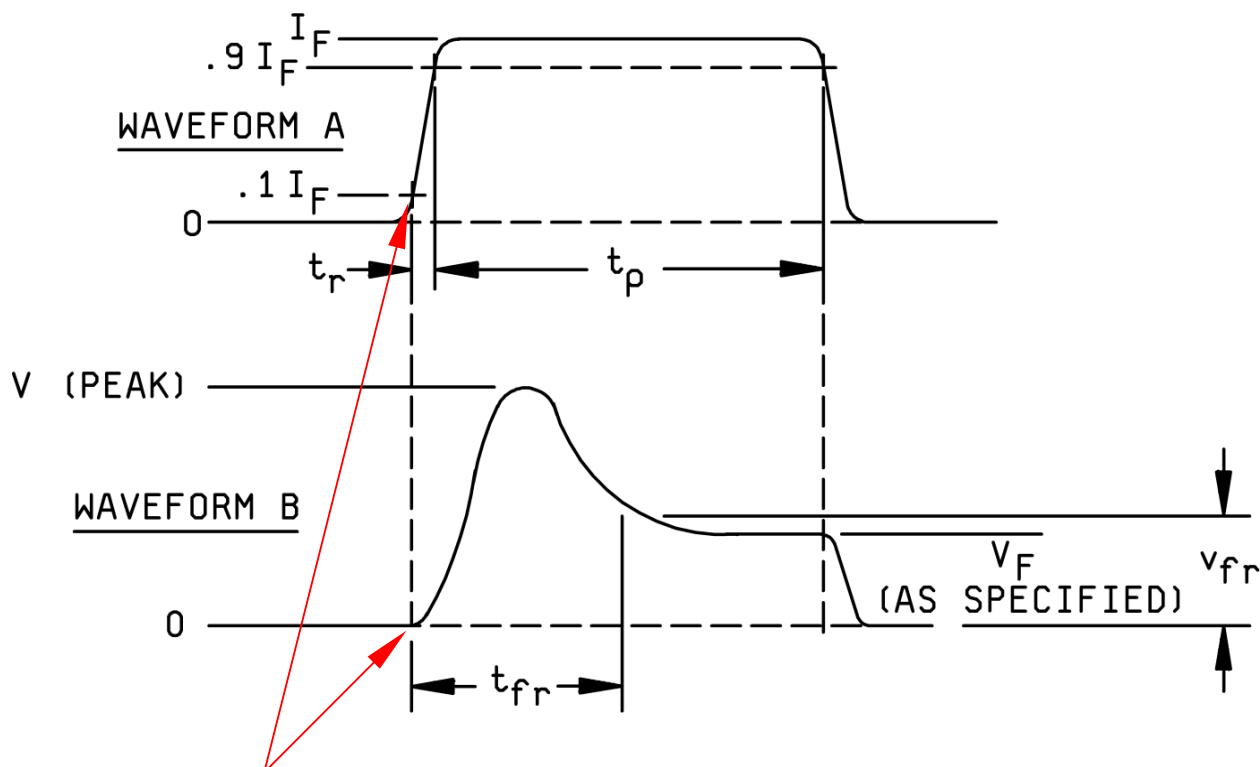
TEL: 888-670-8729 (USA & Canada) or +1-613-686-6675 (Intl)
FAX: 800-561-1970 (USA & Canada) or +1-613-686-6679 (Intl)

info@avtechpulse.com - <http://www.avtechpulse.com/>

☒ BOX 5120, LCD MERIVALE
OTTAWA, ONTARIO
CANADA K2C 3H4

SUGGESTIONS FOR IMPROVING MIL-STD-750 METHOD 4026.3

MAJOR CONCERN: GIVE t_{fr} A CLEARER, MORE MEASURABLE DEFINITION

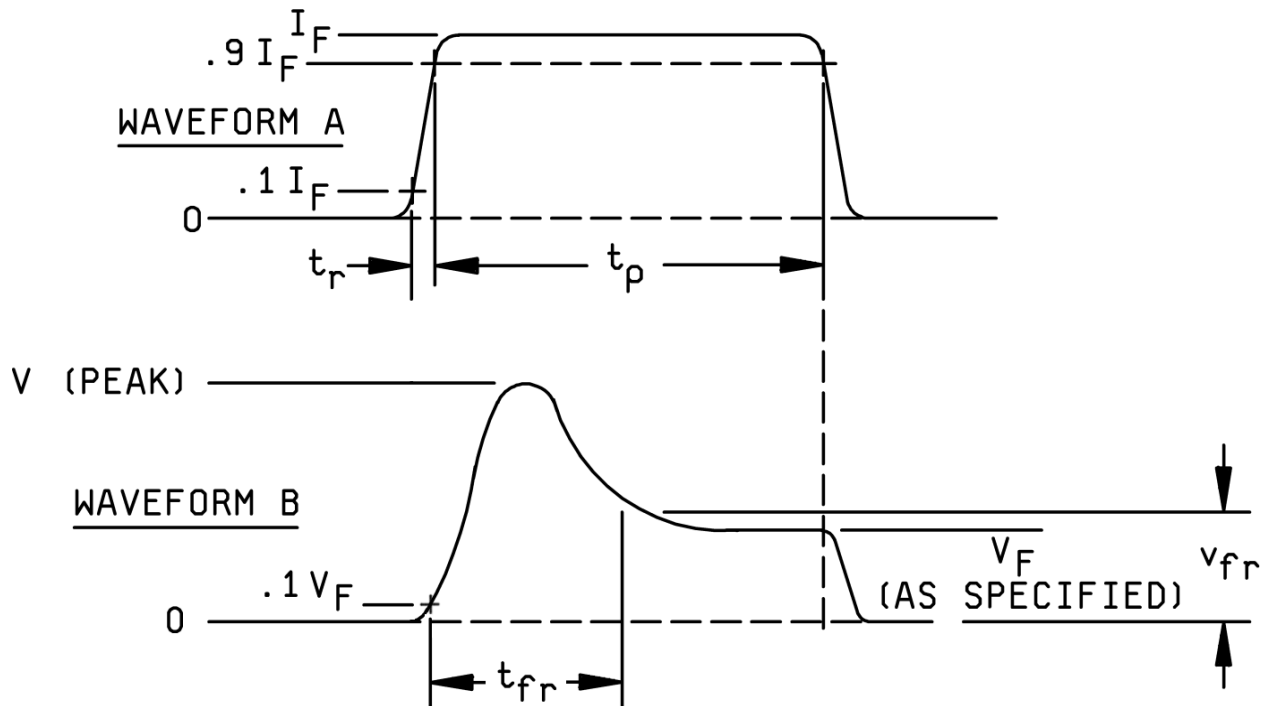


These are not simultaneous, despite the dashed vertical line.

The above figure is ambiguous – it shows t_{fr} as the time between $0.1 I_F$ and $V = V_{fr}$, AND as the time between $V=0$ and $V=V_{fr}$. The latter definition agrees with the text, which says t_{fr} is “measured from the time forward voltage becomes positive to the time that forward voltage recovers to a specified v_{fr} ”.

Unfortunately, it is impossible to measure the “time forward voltage becomes positive” repeatably. Does this mean 1 μV ? 1 mV? 10 mV? Also, this definition makes the measurement highly sensitive to noise and any minor variations in the exact shape of the rising slope (caused, for example, by repositioning a cable). In practice, this results in variations of several nanoseconds, which is problematic for fast devices.

I would suggest measuring t_{fr} between $V = 0.1 V_f$ (or $0.1 V_{fr}$) and $V = V_{fr}$, as shown in the next figure:



This is much easier to measure reliably with automated equipment than the existing definition.

Since this gives a slightly smaller value of t_{fr} , all devices that passed tests based on the old definition would also pass based on the new definition.

MINOR CONCERN: RESPONSE DETECTOR INPUT IMPEDANCE

Method 4026.3 currently calls for $Z \geq 100 R_F$. For a diode tested at $R_F = 0.7V / 100 \text{ mA}$, this gives $Z \geq 700 \text{ Ohms}$. For a diode tested at $R_F = 0.7V / 1 \text{ A}$, this gives $Z \geq 70 \text{ Ohms}$.

In practice, it is convenient to use $Z = 500 \text{ Ohms}$, consisting of a 450 Ohm resistor in series with the 50 Ohm input impedance of an oscilloscope. This provides a 10:1 attenuation ratio, which is convenient for quick calculations.

Also, using higher values of Z with a 50 Ohm oscilloscope results in higher attenuation ratios, which is undesirable due to the small signal levels. For instance, a $V_F = 0.7V$ is attenuated to 70 mV in a 10:1 system. Measuring signals much smaller than that on most oscilloscopes becomes difficult, since DC offsets and noise in common oscilloscopes can amount to several mV or more.

In practice, 500 Ohms is sufficiently high to not affect the measurement, and sufficiently low to not over-attenuate the signal.

I would suggest changing the requirement to $Z \geq 500 \text{ Ohms}$.

This should not affect measured t_{FR} / V_{FR} values in any significant way.

MINOR CONCERN: GENERATOR RESISTANCE

Method 4026.3 currently calls for $R_S \geq 20 R_F$ ($R_F = V_F/I_F$ at specified I_F). For a diode tested at $R_F = 0.7V / 100 \text{ mA}$, this gives $Z \geq 140 \text{ Ohms}$. For a diode tested at $R_F = 0.7V / 1 \text{ A}$, this gives $Z \geq 14 \text{ Ohms}$.

In practice, it is convenient to use a pulse generator with a 50 Ohm output impedance, and install 50 Ohms on the test jig in series with the diode under test, with 50 Ohm coaxial cabling between the pulser and the test jig. This terminates the cabling at both ends, absorbing reflections.

This gives $R_S = 50 \text{ Ohms} + 50 \text{ Ohms} = 100 \text{ Ohms}$, which is lower than the currently-required 140 Ohm value for 100 mA devices.

I would suggest changing the requirement to:

$R_S \geq 10 R_F$

or

$R_S \geq 100 \text{ Ohms}$

This should not affect measured t_{FR} / V_{FR} values in any significant way.

– Dr. Michael J. Chudobiak
mjc@avtechpulse.com
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